

Silicon NPN Power Transistors

2SD201

DESCRIPTION

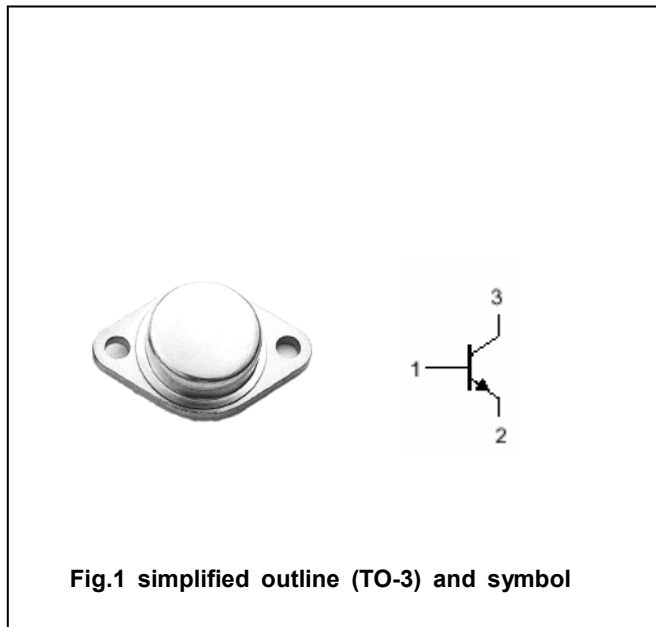
- With TO-3 package
- Large current capability
- Wide area of safe operation

APPLICATIONS

- For power amplifier and switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	90	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
P_C	Collector power dissipation	$T_C = 25 \square$	50	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-55~150	\square

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =50mA ; I _B =0	60			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A ; I _B =0.5A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =90V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =4V	40			
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		8		MHz

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)